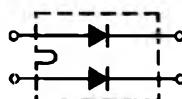


# Fast Recovery Epitaxial Diodes (FRED)

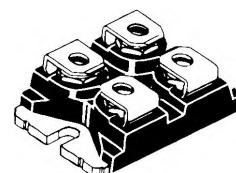
## DSEI 2x121

$I_{FAVM} = 2 \times 123 \text{ A}$   
 $V_{RRM} = 200 \text{ V}$   
 $t_{rr} = 35 \text{ ns}$

$V_{RSM}$	$V_{RRM}$	Type
$V$	$V$	
200	200	DSEI 2x121-02A



miniBLOC, SOT-227 B



Symbol	Test Conditions		Maximum Ratings (per diode)	
$I_{FRMS}$	$T_{VJ} = T_{VJM}$		150	A
$I_{FAVM}^*$	$T_c = 70^\circ\text{C}$ ; rectangular, $d = 0.5$		123	A
$I_{FRM}$	$t_p < 10 \mu\text{s}$ ; rep. rating, pulse width limited by $T_{VJM}$		600	A
$I_{FSM}$	$T_{VJ} = 45^\circ\text{C}$ ; $t = 10 \text{ ms}$ (50 Hz), sine		1200	A
	$t = 8.3 \text{ ms}$ (60 Hz), sine		1300	A
	$T_{VJ} = 150^\circ\text{C}$ ; $t = 10 \text{ ms}$ (50 Hz), sine		1080	A
	$t = 8.3 \text{ ms}$ (60 Hz), sine		1170	A
$\int i^2 dt$	$T_{VJ} = 45^\circ\text{C}$ ; $t = 10 \text{ ms}$ (50 Hz), sine		7200	$\text{A}^2\text{s}$
	$t = 8.3 \text{ ms}$ (60 Hz), sine		7100	$\text{A}^2\text{s}$
	$T_{VJ} = 150^\circ\text{C}$ ; $t = 10 \text{ ms}$ (50 Hz), sine		5800	$\text{A}^2\text{s}$
	$t = 8.3 \text{ ms}$ (60 Hz), sine		5700	$\text{A}^2\text{s}$
$T_{VJ}$			-40...+150	$^\circ\text{C}$
$T_{VJM}$			150	$^\circ\text{C}$
$T_{stg}$			-40...+150	$^\circ\text{C}$
$P_{tot}$	$T_c = 25^\circ\text{C}$		250	W
$V_{ISOL}$	50/60 Hz, RMS $I_{ISOL} \leq 1 \text{ mA}$		2500	$\text{V}_\text{~}$
$M_d$	Mounting torque Terminal connection torque (M4)	1.5/13 1.5/13	Nm/lb.in. Nm/lb.in.	
Weight		30	g	

Symbol	Test Conditions		Characteristic Values (per diode)	
	typ.		max.	
$I_R$	$T_{VJ} = 25^\circ\text{C}$	$V_R = V_{RRM}$	1	mA
	$T_{VJ} = 25^\circ\text{C}$	$V_R = 0.8 \cdot V_{RRM}$	0.5	mA
	$T_{VJ} = 125^\circ\text{C}$	$V_R = 0.8 \cdot V_{RRM}$	20	mA
$V_F$	$I_F = 120 \text{ A}$ ; $T_{VJ} = 150^\circ\text{C}$		0.89	V
	$T_{VJ} = 25^\circ\text{C}$		1.10	V
$V_{T0}$	For power-loss calculations only		0.7	V
$r_T$	$T_{VJ} = T_{VJM}$		2.1	$\text{m}\Omega$
$R_{thJC}$			0.5	K/W
$R_{thCK}$		0.1		K/W
$t_{rr}$	$I_F = 1 \text{ A}$ ; $-di/dt = 400 \text{ A}/\mu\text{s}$ ; $V_R = 30 \text{ V}$ ; $T_{VJ} = 25^\circ\text{C}$	35	50	ns
$I_{RM}$	$V_R = 100 \text{ V}$ ; $I_F = 100 \text{ A}$ ; $-di_F/dt = 200 \text{ A}/\mu\text{s}$ $L \leq 0.05 \mu\text{H}$ ; $T_{VJ} = 100^\circ\text{C}$	12	15	A

\*  $I_{FAVM}$  rating includes reverse blocking losses at  $T_{VJM}$ ,  $V_R = 0.8 V_{RRM}$ , duty cycle  $d = 0.5$

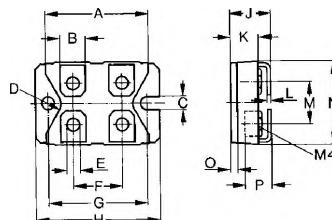
Data according to DIN/IEC 747

IXYS reserves the right to change limits, test conditions and dimensions

### Features

- International standard package miniBLOC (ISOTOP compatible)
- Isolation voltage 2500 V~
- UL registered E 72873
- 2 independent FRED in 1 package
- Planar passivated chips
- Very short recovery time
- Extremely low switching losses
- Low  $I_{RM}$ -values
- Soft recovery behaviour

miniBLOC, SOT-227 B



M4 screws (4x) supplied

Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	31.5	31.7	1.241	1.249
B	7.8	8.2	0.307	0.323
C	4.0	-	0.158	-
D	4.1	4.3	0.162	0.169
E	4.1	4.3	0.162	0.169
F	14.9	15.1	0.587	0.595
G	30.1	30.3	1.186	1.193
H	38.0	38.2	1.497	1.505
J	11.8	12.2	0.465	0.481
K	8.9	9.1	0.351	0.359
L	0.75	0.85	0.030	0.033
M	12.6	12.8	0.496	0.504
N	25.2	25.4	0.993	1.001
O	1.95	2.05	0.077	0.081
P	-	5.0	-	0.197

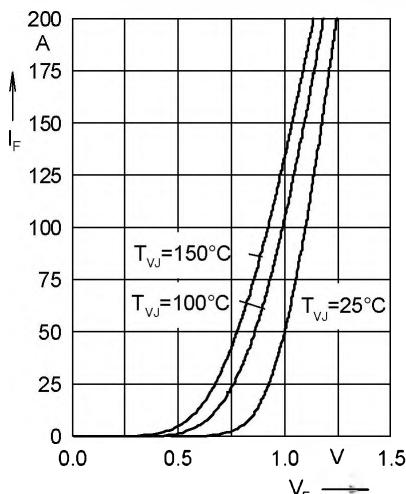


Fig. 1 Forward current  $I_F$  versus  $V_F$

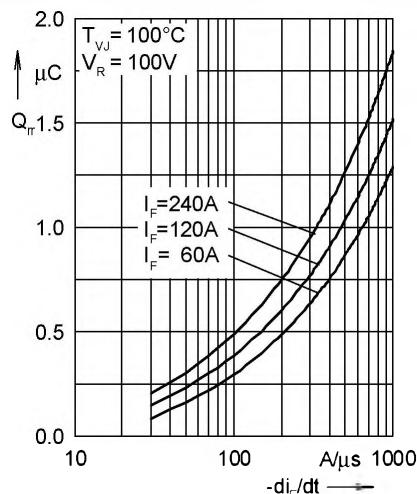


Fig. 2 Reverse recovery charge  $Q_{rr}$  versus  $-di_F/dt$

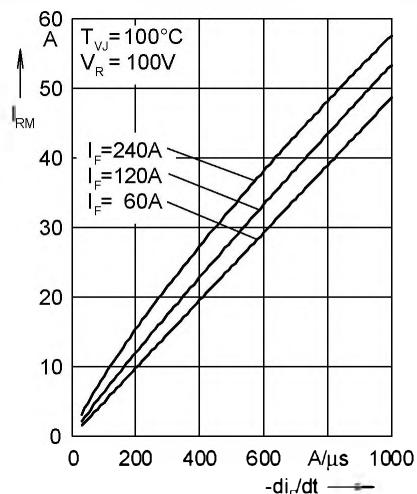


Fig. 3 Peak reverse current  $I_{RM}$  versus  $-di_F/dt$

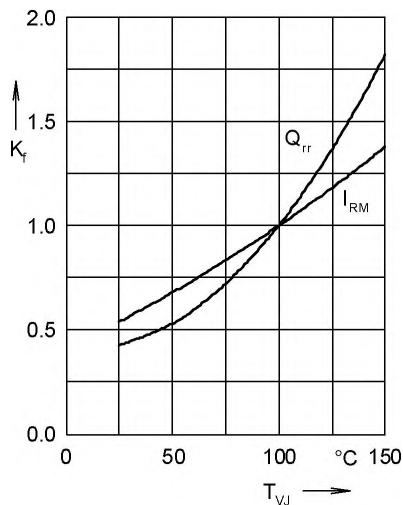


Fig. 4 Dynamic parameters  $Q_{rr}$ ,  $I_{RM}$  versus  $T_{VJ}$

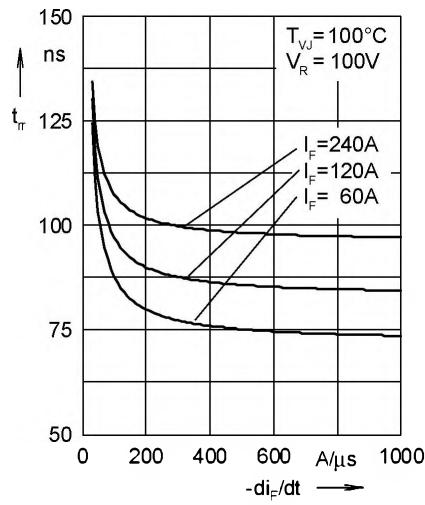


Fig. 5 Recovery time  $t_{rr}$  versus  $-di_F/dt$

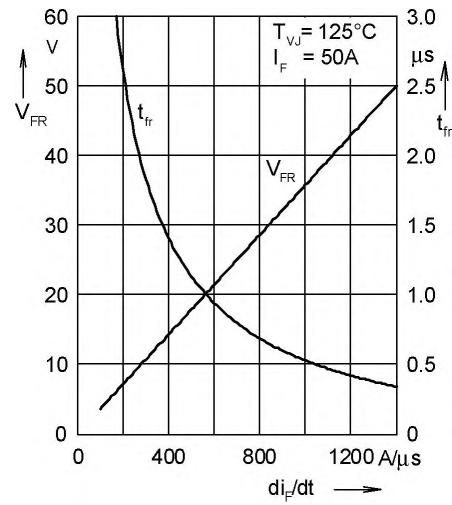


Fig. 6 Peak forward voltage  $V_{FR}$  and  $t_{rr}$  versus  $di_F/dt$

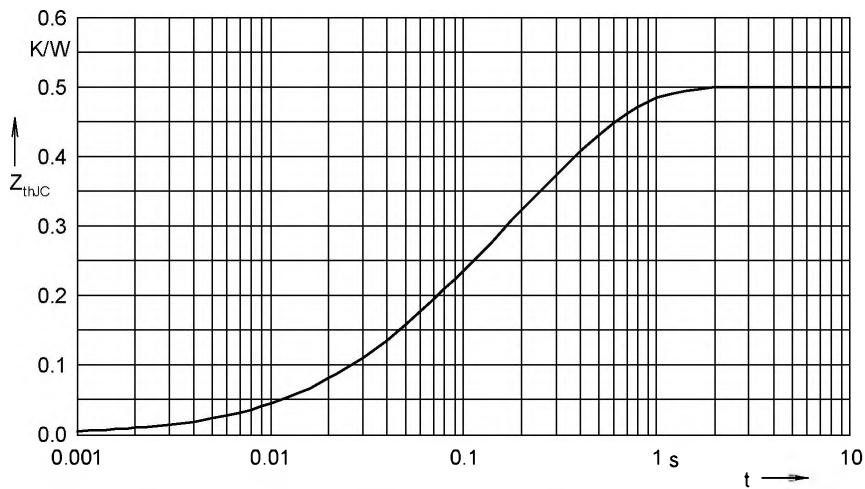


Fig. 7 Transient thermal impedance junction to case

Constants for  $Z_{thJC}$  calculation:

i	$R_{thi}$ (K/W)	$t_i$ (s)
1	0.109	0.028
2	0.214	0.092
3	0.429	0.35